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(54) Title: SETUP METHOD FOR ADJUSTING THE TEMPERATURE CONDITIONS OF AN EPITAXY PROCESS

(57) Abstract: The invention concerns a setup method for an epitaxy process to form a silicon layer, comprising : a) selecting a type of test substrate among silicon based wafers : - having a thickness between 20% and 40% less than a usual thickness for a given substrate diameter, and/or - having an interstitial oxygen concentration of less than 10 ppma ASTM'79, and/or - comprising a SOI stack including a dielectric layer and a thin film of monocrystalline silicon with a thickness less than or equal to 300nm; b) fixing initial temperature conditions, said conditions defining temperatures to be applied to -at least-two areas; c) forming the layer on a test substrate of the selected type, by applying the epitaxy process with the initial temperature conditions; then, measuring slip line defects; d) fixing new temperature conditions by varying the temperatures to be applied to the -at least- two areas of the substrate; f) comparing the quantity of slip line defects measured on the test structures and choosing the temperature conditions generating the fewest slip line defects.



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